

MAINTENANCE MANUAL

138-174 MHz EXCITER BOARD 19D416859G1-G4

LBI 30422A
 (DF 3165)
 (DF 3171 IMTS)

TABLE OF CONTENTS

DESCRIPTION	Page
DESCRIPTION	1
CIRCUIT ANALYSIS	1
OUTLINE DIAGRAM	6
SCHEMATIC DIAGRAM	7
PARTS LIST AND PRODUCTION CHANGES	8
ILLUSTRATIONS	
Figure 1 - Typical Crystal Characteristics	2
Figure 2 - Equivalent ICOM Circuit	3
Figure 3 - Simplified Audio IC	3

DESCRIPTION

This exciter for MASTR[™] II uses nine transistors and one integrated circuit to drive the PA assembly. The exciter can be equipped with up to eight Integrated Circuit Oscillator Modules (ICOMs). The ICOM crystal frequency ranges from approximately 11.5 to 14.5 megahertz, and the crystal frequency is multiplied 12 times.

Audio, supply voltages and control functions are connected from the system board to the exciter board through P902.

Centralized metering jack J103 is provided for use with GE Test Set Model 4EX3A11 or Test Kit 4EX8K12. The test set meters the modulator, multiplier, and amplifier stages, and the regulated 10-Volts.

- 2C-ICOM - contains an oscillator and a 2 PPM ($\pm 0.0002\%$) compensator IC. Will not provide compensation for an EC-ICOM.

The ICOMs are enclosed in an RF shielded can with the type ICOM (5C-ICOM, EC-ICOM or 2C-ICOM) printed on the top of the can. Access to the oscillator trimmer is obtained through a hole on the top of the can.

NOTE

For proper operation, be sure ICOM case makes contact with fingers on the RF shield on the exciter board. Also, the pins on the exciter bottom cover must make contact with the RF shield.

Frequency selection is accomplished by switching the ICOM keying lead (terminal 6) to A- by means of the frequency selector switch on the control unit. In single-frequency radios, a jumper from H9 to H10 in the control unit connects terminal 6 of the ICOM to A-. The oscillator is turned on by applying a keyed +10 Volts to the external oscillator load resistor.

CAUTION

All ICOMs are individually compensated at the factory and cannot be repaired in the field. Any attempt to repair or change an ICOM frequency will void the warranty.

CIRCUIT ANALYSIS

ICOMS

Three different types of ICOMs are available for use in the exciter. Each of the ICOMs contains a crystal-controlled Colpitts oscillator, and two of the ICOMs contain compensator ICs. The different ICOMs are:

- 5C-ICOM - contains an oscillator and a 5 part-per-million ($\pm 0.0005\%$) compensator IC. Provides compensation for EC-ICOMs.
- EC-ICOM - contains an oscillator only. Requires external compensation from a 5C-ICOM.

In Standard 5 PPM radios using EC-ICOMs, at least one 5C-ICOM must be used. The 5C-ICOM is normally used in the receiver F1 position, but can be used in any

transmit or receive position. One 5C-ICOM can provide compensation for up to 15 EC-ICOMs in the transmit and receiver. Should the 5C-ICOM compensator fail in the open mode, the EC-ICOMs will still maintain 2 PPM frequency stability from 0°C to 55°C (+32°F to 131°F) due to the regulated compensation voltage (5 Volts) from the 10-Volt regulator IC. If desired, up to 16 5C-ICOMs may be used in the radio.

The 2C-ICOMs are self-compensated at 2 PPM and will not provide compensation for EC-ICOMs.

Oscillator Circuit

The quartz crystals used in ICOMs exhibit the traditional "S" curve characteristics of output frequency versus operating temperature.

At both the coldest and hottest temperatures, the frequency increases with increasing temperature. In the middle temperature range (approximately 0°C to +55°C), frequency decreases with increasing temperature.

Since the rate of change is nearly linear over the mid-temperature range, the output frequency change can be compensated by choosing a parallel compensation capacitor with a temperature coefficient approximately equal and opposite that of the crystal.

Figure 1 shows the typical performance of an uncompensated crystal as well as the typical performance of a crystal which has been matched with a properly chosen compensation capacitor.

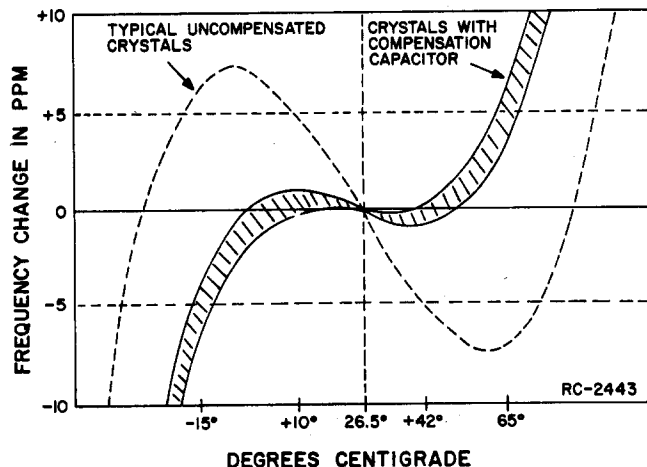


Figure 1 - Typical Crystal Characteristics

At temperatures above and below the mid-range, additional compensation must be introduced. An externally generated compensation voltage is applied to a varactor

(voltage-variable capacitor) which is in parallel with the crystal.

A constant bias of 5 Volts (provided from Regulator IC U901 in parallel with the compensator) established the varactor capacity at a constant value over the entire mid-temperature range. With no additional compensation, all of the oscillators will provide 2 PPM frequency stability from 0°C to 55°C (+32°F to 131°F).

Compensator Circuits

Both the 5C-ICOMs and 2C-ICOMs are temperature compensated at both ends of the temperature range to provide instant frequency compensation. An equivalent ICOM circuit is shown in Figure 2.

The cold end compensation circuit does not operate at temperatures above 0°C. When the temperature drops below 0°C, the circuit is activated. As the temperature decreases, the equivalent resistance decreases and the compensation voltage increases.

An increase in compensation voltage decreases the capacitance of the varactor in the oscillator, thereby increasing the output frequency of the ICOM.

The hot end compensation circuit does not operate at temperatures below +55°C. When the temperature rises above +55°C, the circuit is activated. As the temperature increases, the equivalent resistance decreases and the compensation voltage decreases. The decrease in compensation voltage increases the capacity of the varactor, decreasing the output frequency of the ICOM.

SERVICE NOTE: Proper ICOM operation is dependent on the closely-controlled input voltages from the 10-Volt regulator. Should all of the ICOMs shift off frequency, check the 10-Volt regulator module.

AUDIO IC

The transmitter audio circuitry is contained in audio IC U101. A simplified drawing of the audio IC is shown in Figure 3.

Audio from the microphone at pin 12 is coupled through pre-emphasis capacitor C1 to the base of Q1 in the operational amplifier-limiter circuit. Collector voltage for the transistorized microphone pre-amplifier is supplied from pin 11 through microphone collector load resistor R18 to pin 12.

The operational amplifier-limiter circuit consists of Q1, Q2, and Q3. Q3 provides limiting at high signal levels. The gain of the operational amplifier circuit is fixed by negative feedback through R19, R20 and the resistance in the network (Pin 9).

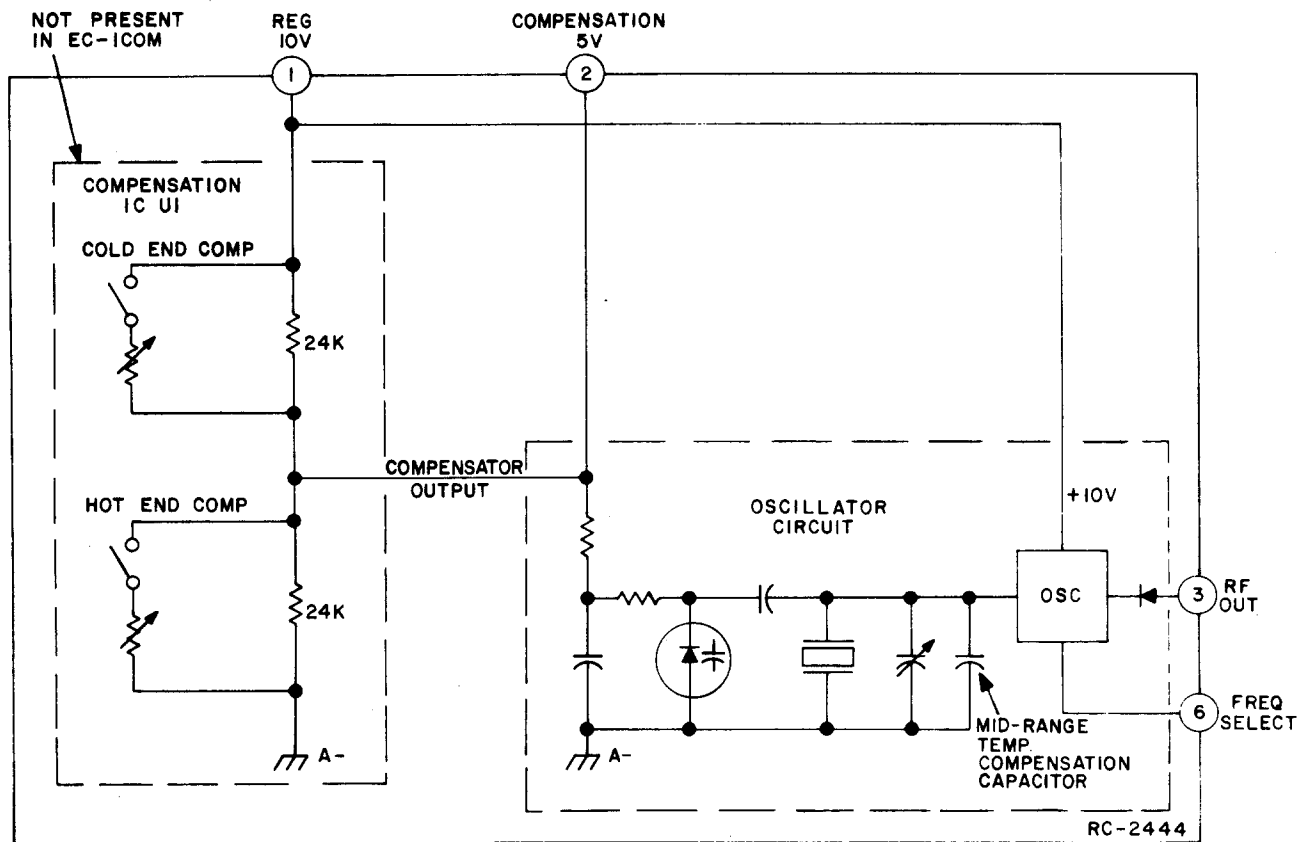


Figure 2 - Equivalent ICOM Circuit

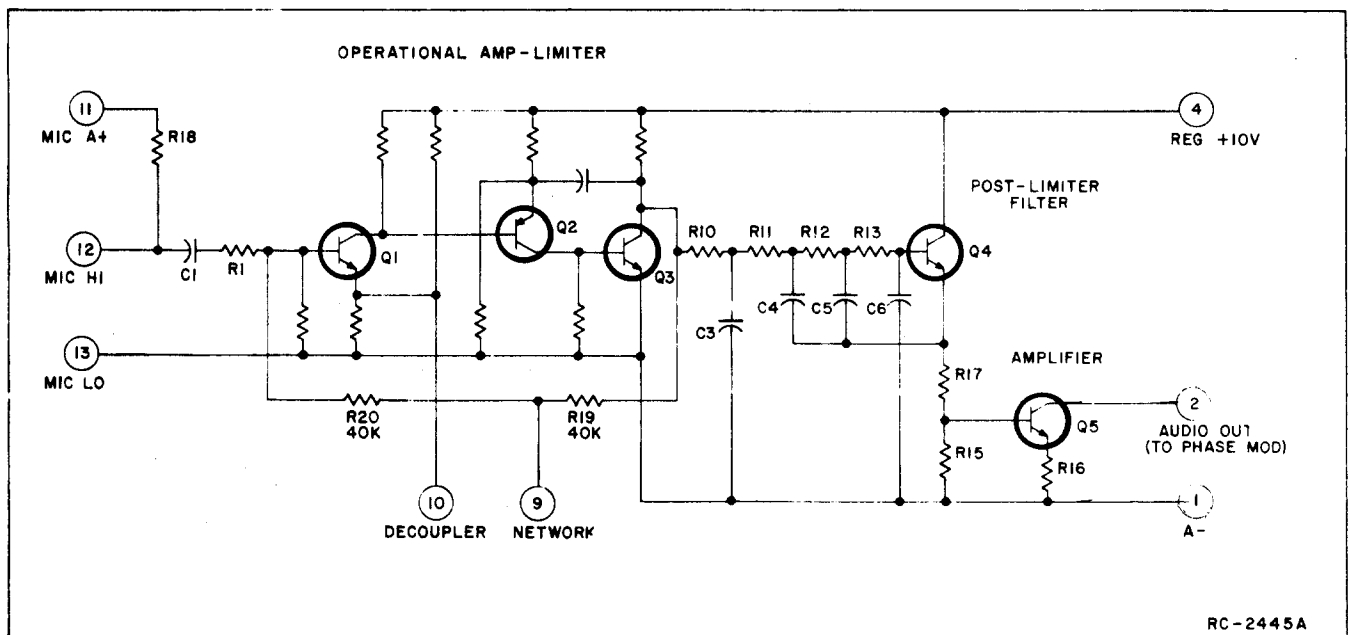


Figure 3 - Simplified Audio IC

The output of Q3 is coupled through a de-emphasis network (R10 and C3) to an active post-limiter filter consisting of C4, C5, C6, R11, R12, R13, R15, R17 and Q4.

Following the post-limiter filter is class A amplifier Q5. The output of Q5 is coupled through MOD ADJUST potentiometer R104 and resistors R108 and R125 to the phase modulators.

SERVICE NOTE: If the DC voltages to the Audio IC are correct and no audio output can be obtained, replace U101.

For radios equipped with Channel Guard, tone from the encoder is applied to the phase modulators through CHANNEL GUARD MOD ADJUST potentiometer R105, and resistors R112, R105 and R127. Instructions for setting R105 are contained in the modulation adjustment section of the Transmitter Alignment Procedure.

BUFFER, PHASE MODULATORS & AMPLIFIERS

The output at pin 3 of the selected ICOM is coupled through buffer-amplifier Q101 to the first modulator stage. The first phase modulator is varactor (voltage-variable capacitor) CV101 in series with tunable coil T101. This network appears as a series-resonant circuit to the RF output of the oscillator. An audio signal applied to the modulator circuit through blocking capacitor C107 varies the bias of CV101, resulting in a phase modulated output. A voltage divider network (R110 and R111) provides the proper bias for varactors CV101, CV102 and CV103.

The output of the first modulator is coupled through blocking capacitor C113 to the base of Class A amplifier Q102. The first modulator stage is metered through a metering network consisting of C115, R118,

and CR101. Diodes CR102 and CR103 remove any amplitude modulation in the modulator output.

Following Q102 is another Class A amplifier, Q103. The output of Q103 is applied to the second modulator stage. The second modulator consists of two cascaded modulator circuits consisting of CV102, T102, T103 and CV103. Following the second modulator is a Class A amplifier, Q104. The output of the second modulator stage is metered through C123, R132, and CR104 and is applied to the base of buffer Q105. Diodes CR105 and CR106 remove any amplitude modulation in the second modulator output.

BUFFER, MULTIPLIERS & AMPLIFIER

Buffer Q105 is saturated when no RF signal is present. Applying an RF signal to Q105 provides a sawtooth waveform at its collector to drive the class C tripler, Q106. The tripler stage is metered through R138. The output of Q106 is coupled through tuned circuits T104 and T105 to the base of doubler Q107. T104 and T105 are tuned to one-fourth of the operating frequency. The doubler stage is metered through R141.

The output of Q107 is coupled through tuned circuits T106 and T107 to the base of second doubler Q108. T106 and T107 are tuned to one-half the operating frequency. Q108 is metered through R146.

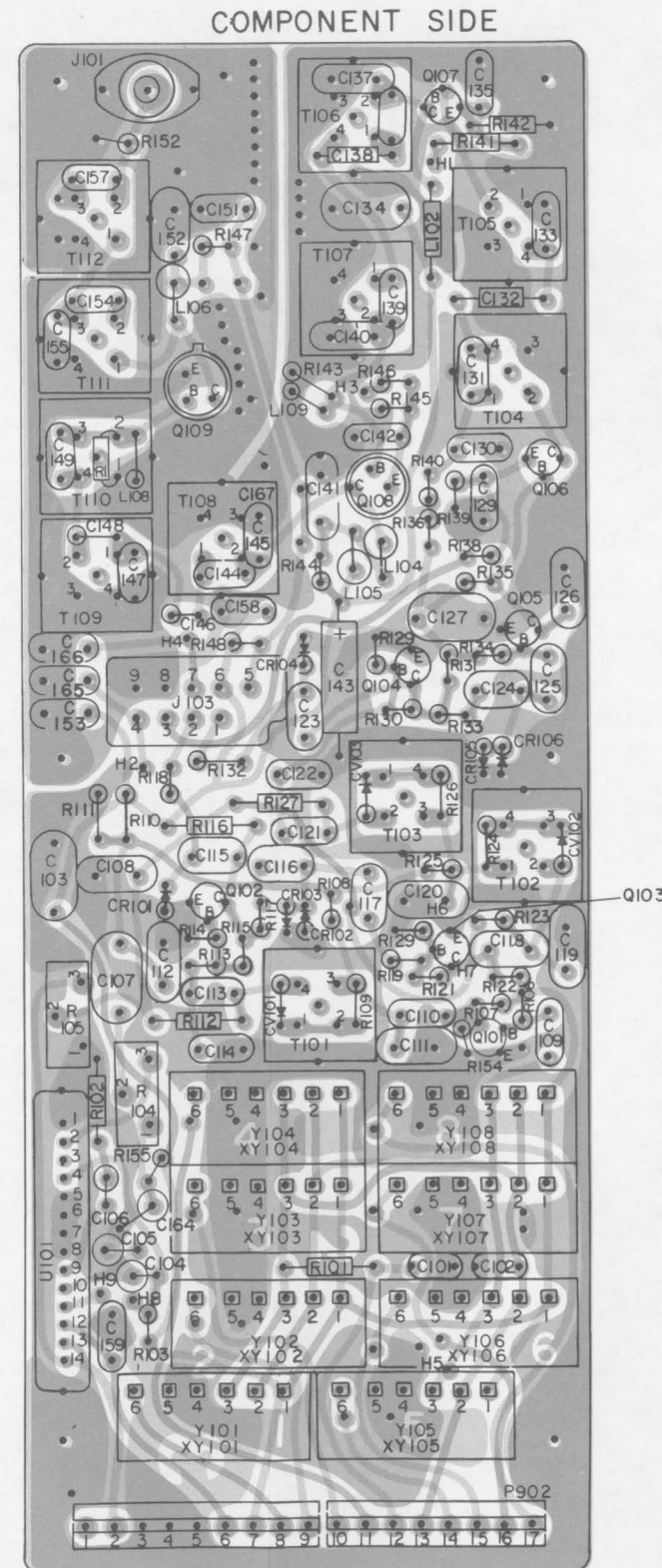
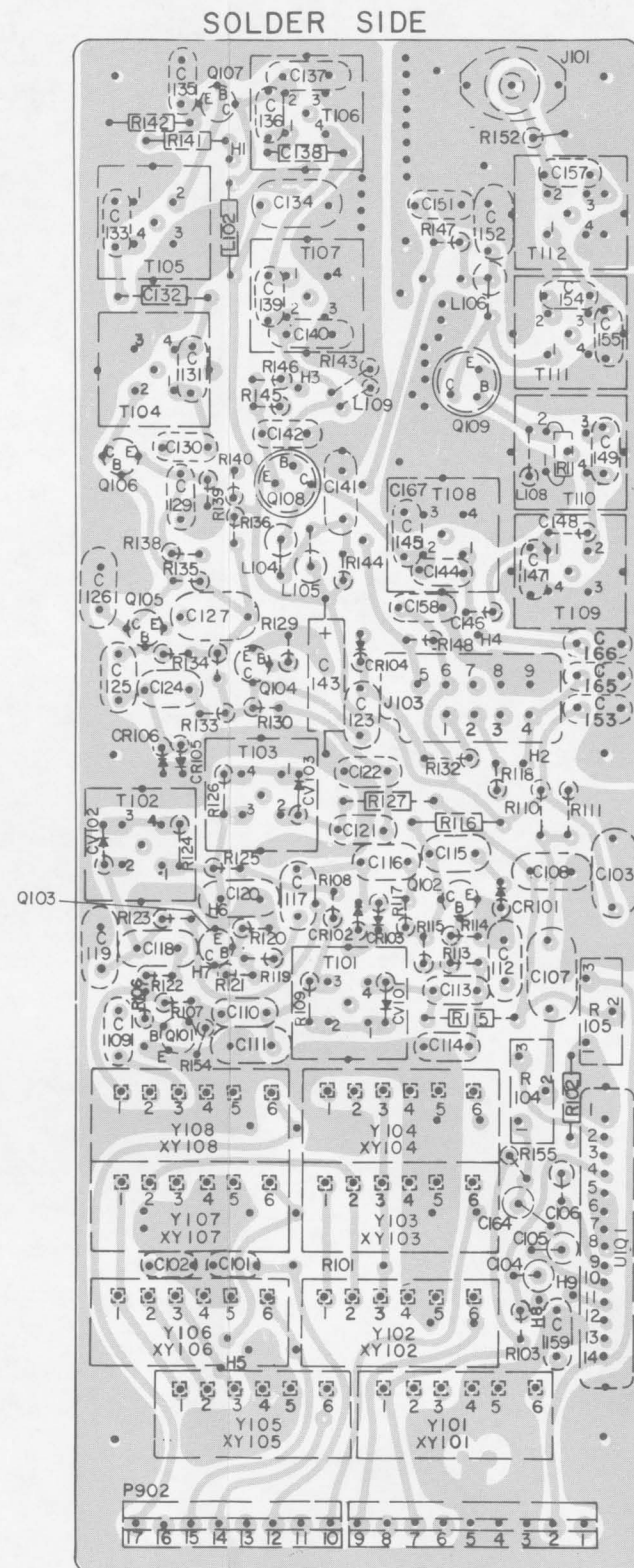
The output of Q108 is coupled through three tuned circuits (T108, T109 and T110) to the base of amplifier Q109. The circuits are tuned to the transmitter operating frequency.

Q109 is a class C amplifier, and is metered through R148. The amplifier collector circuit consists of T111, C154, C155, T112, and C157, and matches the amplifier output to the input of the power amplifier assembly.

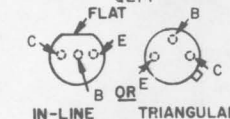
MOBILE RADIO DEPARTMENT
GENERAL ELECTRIC COMPANY • LYNCHBURG, VIRGINIA 24502

GENERAL  ELECTRIC

EXCITER BOARD



LEAD IDENTIFICATION
FOR Q101 - Q109, Q208, Q213,
Q214



NOTE: LEAD ARRANGEMENT, AND NOT CASE SHAPE, IS DETERMINING FACTOR FOR LEAD IDENTIFICATION.

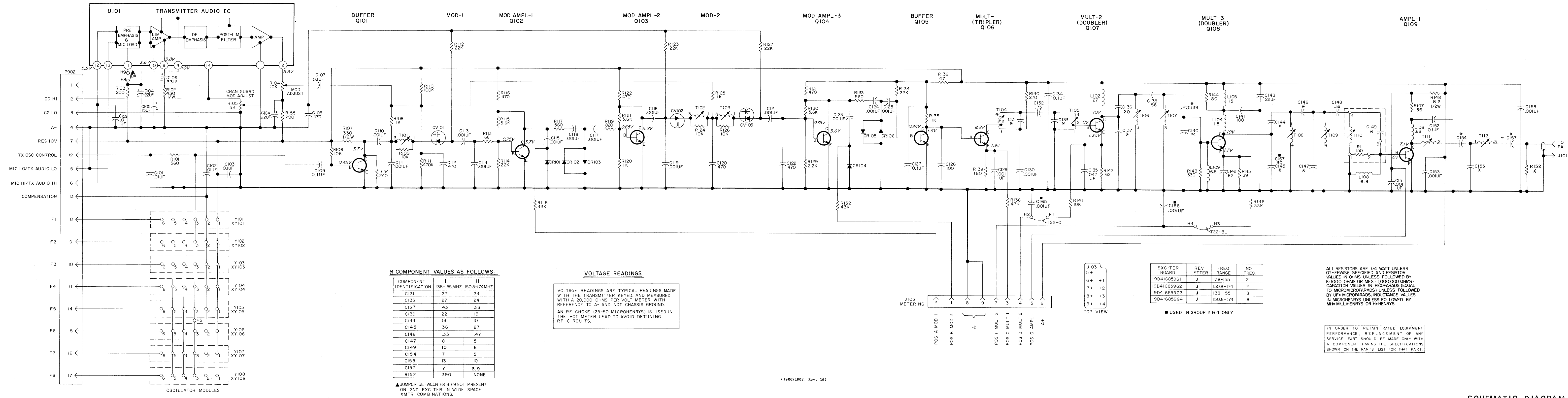
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(19D424489, Rev. 1)

OUTLINE DIAGRAM

138—174 MHz, EXCITER BOARD
19D416859G1-G4



SYMBOL	GE PART NO.	DESCRIPTION
		LBI-4554H 138-174 MHz EXCITER BOARD 19D416859G1-04
		----- CAPACITORS ----- C101 and C102 19A116080P1 Polyester: 0.01 μ f \pm 20%, 50 VDCW. C103 19A116080P107 Polyester: 0.1 μ f \pm 10%, 50 VDCW. C104 5496267P10 Tantalum: 22 μ f \pm 20%, 15 VDCW; sim to Sprague Type 150D. C105 5496267P14 Tantalum: 15 μ f \pm 20%, 20 VDCW; sim to Sprague Type 150D. C106 5496267P9 Tantalum: 3.3 μ f \pm 20%, 15 VDCW; sim to Sprague Type 150D. C107 19A116080P107 Polyester: 0.1 μ f \pm 10%, 50 VDCW. C108 5494481P107 Ceramic disc: 470 pf \pm 20%, 1000 VDCW; sim to RMC Type JF Discap. C109* 19A116080P107 Polyester: 0.1 μ f \pm 10%, 50 VDCW. In G1, G3 of REV C and earlier: In G2, G4 of REV B and earlier: 5494481P111 Ceramic disc: 1000 pf \pm 20%, 1000 VDCW; sim to RMC Type JF Discap. C110 5494481P111 Ceramic disc: 1000 pf \pm 20%, 1000 VDCW; sim to RMC Type JF Discap. C111 5494481P112 Ceramic disc: 1000 pf \pm 10%, 1000 VDCW; sim to RMC Type JF Discap. C112 5494481P107 Ceramic disc: 470 pf \pm 20%, 1000 VDCW; sim to RMC Type JF Discap. C113 thru C117 5494481P111 Ceramic disc: 1000 pf \pm 20%, 1000 VDCW; sim to RMC Type JF Discap. C118 and C119 5494481P112 Ceramic disc: 1000 pf \pm 10%, 1000 VDCW; sim to RMC Type JF Discap. C120 7489162P43 Silver mica: 470 pf \pm 5%, 300 VDCW; sim to Electro Motive Type DM-15. C121 5494481P112 Ceramic disc: 1000 pf \pm 10%, 1000 VDCW; sim to RMC Type JF Discap. C122 5494481P107 Ceramic disc: 470 pf \pm 20%, 1000 VDCW; sim to RMC Type JF Discap. C123 thru C126 5494481P111 Ceramic disc: 1000 pf \pm 20%, 1000 VDCW; sim to RMC Type JF Discap. C127 7489162P27 Silver mica: 100 pf \pm 5%, 500 VDCW; sim to Electro Motive Type DM-15. C129 and C130 5494481P111 Ceramic disc: 1000 pf \pm 20%, 1000 VDCW; sim to RMC Type JF Discap. C131L 5496219P249 Ceramic disc: 27 pf \pm 5%, 500 VDCW, temp coef -80 PPM. C131H 5496219P248 Ceramic disc: 24 pf \pm 5%, 500 VDCW, temp coef -80 PPM. C132* 5491601P118 Phenolic: 0.75 pf \pm 5%, 500 VDCW. Earlier than REV A: Phenolic: 0.68 pf \pm 5%, 500 VDCW. C133L 5496219P249 Ceramic disc: 27 pf \pm 5%, 500 VDCW, temp coef -80 PPM. C133H 5496219P248 Ceramic disc: 24 pf \pm 5%, 500 VDCW, temp coef -80 PPM. C134 19A116080P107 Polyester: 0.1 μ f \pm 10%, 50 VDCW. C135 19A116080P105 Polyester: 0.047 μ f \pm 10%, 50 VDCW. C136* 5496219P246 Ceramic disc: 20 pf \pm 5%, 500 VDCW, temp coef -80 PPM. Added by REV B.

SYMBOL	GE PART NO.	DESCRIPTION
C136L*	5496219P248	Ceramic disc: 24 pf \pm 5%, 500 VDCW, temp coef -150 PPM. Deleted by REV B.
C136H*	5496219P246	Ceramic disc: 20 pf \pm 5%, 500 VDCW, temp coef -80 PPM. Deleted by REV B.
C137*	5496219P251	Ceramic disc: 33 pf \pm 5%, 500 VDCW, temp coef -80 PPM. Deleted by REV B. Earlier than REV A: Ceramic disc: 27 pf \pm 5%, 500 VDCW, temp coef -80 PPM. C137L* 5496219P254 Ceramic disc: 43 pf \pm 5%, 500 VDCW, temp coef -80 PPM. Added by REV B. C137H* 5496219P251 Ceramic disc: 33 pf \pm 5%, 500 VDCW, temp coef -80 PPM. Added by REV B. C138* 5491601P115 Phenolic: 0.56 pf \pm 5%, 500 VDCW. Earlier than REV A: Phenolic: 0.47 pf \pm 5%, 500 VDCW. C139L 5496219P247 Ceramic disc: 22 pf \pm 5%, 500 VDCW, temp coef -80 PPM. C139H 5496219P243 Ceramic disc: 13 pf \pm 5%, 500 VDCW, temp coef -80 PPM. C140 5496219P348 Ceramic disc: 24 pf \pm 5%, 500 VDCW, temp coef -150 PPM. C141* 5490008P127 Silver mica: 100 pf \pm 10%, 500 VDCW; sim to Electro Motive Type DM-15. Earlier than REV A: Polyester: 0.1 μ f \pm 10%, 50 VDCW. C142 7489162P25 Polyester: 0.1 μ f \pm 10%, 50 VDCW; sim to Electro Motive Type DM-15. C143 5496267P10 Tantalum: 22 μ f \pm 20%, 15 VDCW; sim to Sprague Type 150D. C144L* 5496219P243 Ceramic disc: 13 pf \pm 5%, 500 VDCW, temp coef -80 PPM. In REV A and earlier: Ceramic disc: 15 pf \pm 5%, 500 VDCW, temp coef -80 PPM. C144H 5496219P241 Ceramic disc: 10 pf \pm 0.25 pf, 500 VDCW, temp coef -80 PPM. C145* 5496219P249 Ceramic disc: 27 pf \pm 5%, 500 VDCW, temp coef -80 PPM. Deleted by REV B. Earlier than REV A: Ceramic disc: 20 pf \pm 5%, 500 VDCW, temp coef -80 PPM. C145L* 5496219P252 Ceramic disc: 36 pf \pm 5%, 500 VDCW, temp coef -80 PPM. Added by REV B. C145H* 5496219P249 Ceramic disc: 27 pf \pm 5%, 500 VDCW, temp coef -80 PPM. Added by REV B. Deleted by REV G. C146* 5491601P113 Phenolic: 0.47 pf \pm 5%, 500 VDCW. Deleted by REV B. Earlier than REV A: Phenolic: 0.68 pf \pm 5%, 500 VDCW. C146L* 5491601P109 Phenolic: 0.33 pf \pm 5%, 500 VDCW. Added by REV B. C146H* 5491601P113 Phenolic: 0.47 pf \pm 5%, 500 VDCW. Added by REV B. C147L 5496219P239 Ceramic disc: 8.0 pf \pm 0.25 pf, 500 VDCW, temp coef -80 PPM. C147H 5496219P238 Ceramic disc: 5.0 pf \pm 0.25 pf, 500 VDCW, temp coef -80 PPM. C148* 5491601P111 Phenolic: 0.39 pf \pm 5%, 500 VDCW. Earlier than REV A: Phenolic: 0.68 pf \pm 5%, 500 VDCW. C149L 5496219P241 Ceramic disc: 10 pf \pm 0.25 pf, 500 VDCW, temp coef -80 PPM. C149H 5496219P237 Ceramic disc: 6.0 pf \pm 0.25 pf, 500 VDCW, temp coef -80 PPM. C151 19A116655P19 Ceramic disc: 1000 pf \pm 20%, 1000 VDCW; sim to RMC Type JF Discap. C152 19A116080P107 Polyester: 0.1 μ f \pm 10%, 50 VDCW. C153 19A116655P19 Ceramic disc: 1000 pf \pm 20%, 1000 VDCW; sim to RMC Type JF Discap. C154L 5496219P238 Ceramic disc: 7.0 pf \pm 0.25 pf, 500 VDCW, temp coef -80 PPM. C154H 5496219P236 Ceramic disc: 5.0 pf \pm 0.25 pf, 500 VDCW, temp coef -80 PPM.

SYMBOL	GE PART NO.	DESCRIPTION
C155H 5496219P241		Ceramic disc: 10 pf \pm 0.25 pf, 500 VDCW, temp coef -80 PPM.
C155L 5496219P243		Ceramic disc: 13 pf \pm 5%, 500 VDCW, temp coef -80 PPM.
C157L 5496219P238		Ceramic disc: 7.0 pf \pm 0.25 pf, 500 VDCW, temp coef -80 PPM.
C157H* 5491601P31		Phenolic: 3.9 pf \pm 10%, 500 VDCW. In REV F and earlier: In REV A-H: Ceramic disc: 1000 pf \pm 20%, 1000 VDCW; sim to RMC Type JF Discap. C158 19A116655P19 Ceramic disc: 1000 pf \pm 20%, 1000 VDCW; sim to RMC Type JF Discap. C159* 19A116080P1 Polyester: 0.01 μ f \pm 20%, 50 VDCW. In 19D416859G1, G3 of REV D and earlier: In 19D416859G2, G4 of REV C and earlier: 19A116655P19 Ceramic disc: 1000 pf \pm 20%, 1000 VDCW; sim to RMC Type JF Discap. C164* 5496267P10 Tantalum: 22 μ f \pm 20%, 15 VDCW; sim to Sprague Type 150D. Added to 19D416859G1, G3 by REV F. Added to 19D416859G2, G4 by REV E. C165* and C166* 5494481P111 Ceramic disc: 1000 pf \pm 20%, 1000 VDCW; sim to RMC Type JF Discap. Added by REV G. C167* 5496219P250 Ceramic disc: 30 pf \pm 5%, 500 VDCW, temp coef -80 PPM. Added by REV G. ----- DIODES AND RECTIFIERS ----- CR101 thru CR106 19A115250P1 Silicon. CV101* and CV102* 5495769P9 Silicon, capacitive: 33 pf \pm 10%, at 4 VDC. In 19D416859G1, G3 of REV D and earlier: In 19D416859G2, G4 of REV C and earlier: Silicon, capacitive: 33 pf \pm 20%, at 4 VDC. 5495769P8 Ceramic disc: 15 pf \pm 5%, 500 VDCW, temp coef -80 PPM. CV103* 5495769P9 Silicon, capacitive: 33 pf \pm 10%, at 4 VDC. Added to G2, G4 by REV D; to G1, G3 by REV E. 5495769P8 Silicon, capacitive: 33 pf \pm 20%, at 4 VDC. Deleted by REV B. CV103L* 5495769P9 Silicon, capacitive: 33 pf \pm 10%, at 4 VDC. Added by REV B. Deleted by REV D. CV103H* 5495769P8 Silicon, capacitive: 33 pf \pm 20%, at 4 VDC. Added by REV B. Deleted by REV D. ----- JACKS AND RECEPTACLES ----- J101 19A130924G1 Receptacle, coaxial: sim to Cinch 14H11613. J103 19B219374G1 Connector. Includes: 19A116651P1 Contacts. (9). ----- INDUCTORS ----- L102 19B209420P130 Coil, RF: 27.0 μ h \pm 10%, 3.60 ohms DC res max; sim to Jeffers 4411B-5. L104 7488079P18 Choke, RF: 1.50 μ h \pm 10%, 0.50 ohms DC res max; sim to Jeffers 4411-10K. L105 7488079P18 Choke, RF: 15.0 μ h \pm 10%, 1.20 ohms DC res max; sim to Jeffers 4421-9K. L106 7488079P5 Choke, RF: 0.68 μ h \pm 10%, 0.15 ohms DC res max; sim to Jeffers 4411-5K. L108* 19B209420P123 Coil, RF: 6.80 μ h \pm 10%, 1.80 ohms DC res max; sim to Jeffers 4446-2. Added to low split by REV B. L109* 19B209420P123 Coil, RF: 6.80 μ h \pm 10%, 1.80 ohms DC res max; sim to Jeffers 4446-2. Added by REV A. P802 Includes: Contact strip: 8 pins. 19B219594P2 Contact strip: 9 pins. 19B219594P3 ----- TRANSISTORS ----- Q101* 19A115330P1 Silicon, NPN. In G1, G3 of REV B and earlier: In G2, G4 of REV A and earlier: 19A115910P1 Silicon, NPN; sim to Type 2N3904.

SYMBOL	GE PART NO.	DESCRIPTION
Q102 thru Q106 19A115330P1		Silicon, NPN.
Q107 19A115328P1		Silicon, NPN.
Q108* 19A115329P2		Silicon, NPN. Earlier than REV A: 19A115329P1 Silicon, NPN. 19A116868P1 Silicon, NPN; sim to Type 2N4427. In REV A-H: 19A115329P2 Silicon, NPN. 19A115329P1 Silicon, NPN.
Q109* 19A116868P1		Earlier than REV A: Silicon, NPN. ----- RESISTORS ----- R101 3R152P561K Composition: 560 ohms \pm 10%, 1/4 w. R102* 3R152P431J Composition: 430 ohms \pm 5%, 1/4 w. In 19D416859G1, G3 of REV F and earlier: In 19D416859G2, G4 of REV E and earlier: 3R152P391K Composition: 390 ohms \pm 10%, 1/4 w. 3R152P201J Composition: 200 ohms \pm 5%, 1/4 w. 3R152P102K Composition: 1000 ohms \pm 10%, 1/4 w. R104 19B209358P106 Variable, carbon film: approx 300 to 10,000 ohms \pm 10%, 0.25 w; sim to CTS Type X-201. R105* 19B209358P105 Variable, carbon film: approx 200 to 5000 ohms \pm 10%, 0.25 w; sim to CTS Type X-201. In 19D416859G1, G3 of REV D and earlier: In 19D416859G2, G4 of REV C and earlier: 19B209358P108 Variable, carbon film: approx 2000 to 50,000 ohms \pm 10%, 0.25 w; sim to CTS Type X-201. R106* 3R152P103K Composition: 10,000 ohms \pm 10%, 1/4 w. In G1, G3 of REV B and earlier: In G2, G4 of REV A and earlier: 3R152P393K Composition: 39,000 ohms \pm 10%, 1/4 w. R107* 3R77P331K Composition: 330 ohms \pm 10%, 1/2 w. In 19D416859G1, G3 of REV E and earlier: In 19D416859G2, G4 of REV D and earlier: 3R152P331K Composition: 330 ohms \pm 10%, 1/4 w. R108 3R152P102K Composition: 1000 ohms \pm 10%, 1/4 w. R109 3R152P103K Composition: 10,000 ohms \pm 10%, 1/4 w. R110 3R152P104K Composition: 0.10 megohm \pm 10%, 1/4 w. R111 3R152P474K Composition: 0.47 megohm \pm 10%, 1/4 w. R112 3R152P223K Composition: 22,000 ohms \pm 10%, 1/4 w. R113 3R152P806K Composition: 68 ohms \pm 10%, 1/4 w. R114 3R152P222K Composition: 2200 ohms \pm 10%, 1/4 w. R115 3R152P562K Composition: 5600 ohms \pm 10%, 1/4 w. R116 3R152P471K Composition: 470 ohms \pm 10%, 1/4 w. R117 3R152P661K Composition: 560 ohms \pm 10%, 1/4 w. R118 3R152P433J Composition: 43,000 ohms \pm 5%, 1/4 w. R119 3R152P821K Composition: 820 ohms \pm 10%, 1/4 w. R120 3R152P102K Composition: 1000 ohms \pm 10%, 1/4 w. R121 3R152P562K Composition: 5600 ohms \pm 10%, 1/4 w. R122 3R152P471K Composition: 470 ohms \pm 10%, 1/4 w. R123 3R152P223K Composition: 22,000 ohms \pm 10%, 1/4 w. R124 3R152P103K Composition: 10,000 ohms \pm 10%, 1/4 w. R125 3R152P102K Composition: 1000 ohms \pm 10%, 1/4 w. R126 3R152P103K Composition: 10,000 ohms \pm 10%, 1/4 w. R127 3R152P223K Composition: 22,000 ohms \pm 10%, 1/4 w. R129 3R152P222K Composition: 2200 ohms \pm 10%, 1/4 w. R130 3R152P562K Composition: 5600 ohms \pm 10%, 1/4 w. R131 3R152P471K Composition: 470 ohms \pm 10%, 1/4 w. R132 3R152P433J Composition: 43,000 ohms \pm 5%, 1/4 w.

SYMBOL	GE PART NO.	DESCRIPTION
R133 3R152P561K		Composition: 560 ohms \pm 10%, 1/4 w.
R134* 3R152P223K		Composition: 21,000 ohms \pm 10%, 1/4 w. Earlier than REV A: 3R152P333K Composition: 33,000 ohms \pm 10%, 1/4 w. 3R152P102K Composition: 1000 ohms \pm 10%, 1/4 w. 3R152P470K Composition: 470 ohms \pm 10%, 1/4 w. 3R152P473K Composition: 47,000 ohms \pm 10%, 1/4 w. 3R152P181K Composition: 180 ohms \pm 10%, 1/4 w. Earlier than REV A: 3R152P301J Composition: 300 ohms \pm 5%, 1/4 w. 3R152P271K Composition: 270 ohms \pm 10%, 1/4 w. 3R152P103K Composition: 10,000 ohms \pm 10%, 1/4 w. 3R152P620J Composition: 62 ohms \pm 5%, 1/4 w. 3R152P331K Composition: 330 ohms \pm 10%, 1/4 w. 3R152P181K Composition: 180 ohms \pm 10%, 1/4 w. Earlier than REV A: 3R152P331K Composition: 330 ohms \pm 10%, 1/4 w. 3R152P390K Composition: 39 ohms \pm 10%, 1/4 w. 3R152P470K Composition: 47 ohms \pm 5%, 1/4 w. 3R152P333K Composition: 33,000 ohms \pm 10%, 1/4 w. 3R152P360J Composition: 36 ohms \pm 5%, 1/4 w. In REV H and earlier: 3R152P200J Composition: 20 ohms \pm 5%, 1/4 w. 7147161P42 Composition: 8.2 ohms \pm 5%, 1/2 w. In REV H and earlier: 3R77P100J Composition: 10 ohms \pm 5%, 1/2 w. 3R152P391K Composition: 390 ohms \pm 10%, 1/4 w. Added by REV B. 3R152P241J Composition: 240 ohms \pm 5%, 1/4 w. Added to 19D416859G1, G3 by REV E. Added to 19D416859G2, G4 by REV D. 3R152P201J Composition: 200 ohms \pm 5%, 1/4 w. Added to 19D416859G1, G3 by REV F. Added to 19D416859G2, G4 by REV E. T101* 19D416843G10 Coil. Includes: 5493185P12 Tuning slug. In REV G and earlier: 19D416843G9 Coil. Includes: 5493185P12 Tuning slug. 19D416843G1 Coil. Includes: 5493185P12 Tuning slug. 19D416843G3 Coil. Includes: 5493185P12 Tuning slug. 19D416843G2 Coil. Includes: 5493185P12 Tuning slug. 19D416843G7 Coil. Includes: 5493185P12 Tuning slug. 19D416843G5 Coil. Includes: 5493185P13 Tuning slug. T110 COIL ASSEMBLY 19D416843G8 ----- RESISTORS ----- R1 3R152P151K Composition: 150 ohms \pm 10%, 1/4 w. ----- MISCELLANEOUS ----- 5493185P13 Tuning slug.

SYMBOL	GE PART NO.	DESCRIPTION
T111 19D416843G4		Coil. Includes: 5493185P12 Tuning slug. T112 19D416843G6
		5493185P12 Tuning slug. ----- INTEGRATED CIRCUITS ----- U101 19D416542G2 Audio Transmitter. ----- SOCKETS ----- XY101 thru XY108 19A116779P1 Socket. Part of Mechanical Construction. Includes: Contact, electrical: sim to Molex 08-54-0404. Quantity (6) with each. ----- OSCILLATORS ----- NOTE: When reordering specify ICOM Frequency. ICOM Freq = Operating Frequency 12 Y101 thru Y108 19A129393G17 Externally compensated, \pm 5 PPM, 138-174 MHz. 19A129393G14 Internally compensated, \pm 2 PPM, 138-174 MHz. ----- MECHANICAL PARTS ----- Can. (Used with T101-T112). 4036555P1 Insulator, washer: nylon. (Used with Q108, Q109). 19B227611G1 Exciter PA Interconnecting Cable. (Used in G2, G4 only). REV. A - Exciter Board 19D416859G1, G4 To improve operation. Changed C132, C137, C138, C141, C145, C148, R134, R139, R144, R145, Q108, Q109, and added L109. REV. B - Exciter Board 19D416859G1, G3 To improve operation. Deleted C136L. Changed C136H, C137, C144L, C145, C146, CV103 and added C137L, C145L, C146L, C103L, L108 and R152. REV. C - Exciter Board 19D416859G1, G3 To improve drive to modulator stage. Changed Q101 and R106. REV. D - To Exciter Board 19D416859G1, G3 To reduce transmitter noise. Changed C109. REV. B - Exciter Board 19D416859G2, G4 To improve drive to modulator stage. Changed Q101 and R106. REV. C - Exciter Board 19D416859G2, G4 To reduce transmitter noise. Changed C109. REV. D - Exciter Board 19D416859G2, G4 REV. E - Exciter Board 19D416859G1, G3 To improve operation. Changed CV101, CV102, CV103, C159, and R105. Added R154. REV. E - Exciter Board 19D416859G2, G4 REV. F - Exciter Board 19D416859G1, G3 To reduce attenuation noise and improve operation. Changed R107. Added C164 and R155. REV. F - Exciter Board 19D416859G2, G4 REV. G - Exciter Board 19D416859G1, G3 To increase audio sensitivity. Changed R102. REV. G - Exciter Board 19D416859G2, G4 To reduce conducted spurious in transmitter output. Delete C145H. Added C165, C166 and C167. REV. H - Exciter Board 19D416859G1-4 To improve band-end tuning. Changed T101 from 19D416843G9 to 19D416843G10 REV. J - Exciter Board 19D416859G1-4 To increase RF power output. Changed Q109, R147 and R148.

PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter", which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

REV. A - Exciter Board 19D416859G1, G4

To improve operation. Changed C132, C137, C138, C141, C145, C148, R134, R139, R144, R145, Q108, Q109, and added L109.

REV. B - Exciter Board 19D416859G1, G3

To improve operation. Deleted C136L. Changed C136H, C137, C144L, C145, C146, CV103 and added C137L, C145L, C146L, C103L, L108 and R152.

REV. C - Exciter Board 19D416859G1, G3

To improve drive to modulator stage. Changed Q101 and R106.

REV. D - To Exciter Board 19D416859G1, G3

To reduce transmitter noise. Changed C109.

REV. B - Exciter Board 19D416859G2, G4

To improve drive to modulator stage. Changed Q101 and R106.

REV. C - Exciter Board 19D416859G2, G4

To reduce transmitter noise. Changed C109.

REV. D - Exciter Board 19D416859G2, G4

REV. E - Exciter Board 19D416859G1, G3

To improve operation. Changed CV101, CV102, CV103, C159, and R105. Added R154.

REV. E - Exciter Board 19D416859G2, G4

REV. F - Exciter Board 19D416859G1, G3

To reduce attenuation noise and improve operation. Changed R107. Added C164 and R155.

REV. F - Exciter Board 19D416859G2, G4

REV. G - Exciter Board 19D416859G1, G3

To increase audio sensitivity. Changed R102.

REV. G - Exciter Board 19D416859G2, G4

To reduce conducted spurious in transmitter output. Delete C145H. Added C165, C166 and C167.

REV. H - Exciter Board 19D416859G1-4

To improve band-end tuning. Changed T101 from 19D416843G9 to 19D416843G10

REV. J - Exciter Board 19D416859G1-4

To increase RF power output. Changed Q109, R147 and R148.